

IRFR220B / IRFU220B

200V N-Channel MOSFET

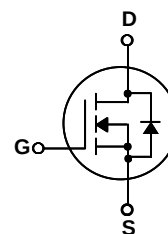
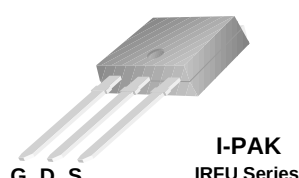
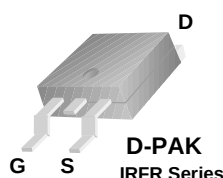
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supply and motor control.

Features

- 4.6A, 200V, $R_{DS(on)} = 0.8\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 12 nC)
- Low C_{rss} (typical 10 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	IRFR220B / IRFU220B	Units
V_{DSS}	Drain-Source Voltage	200	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	4.6	A
	- Continuous ($T_C = 100^\circ\text{C}$)	2.9	A
I_{DM}	Drain Current - Pulsed (Note 1)	18	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	65	mJ
I_{AR}	Avalanche Current (Note 1)	4.6	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	4.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	2.5	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	40	W
	- Derate above 25°C	0.32	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	3.14	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	$^\circ\text{C/W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics

 $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.2	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.3\text{ A}$	--	0.65	0.8	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 2.3\text{ A}$ (Note 4)	--	3.7	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	300	390	pF
C_{oss}	Output Capacitance		--	50	65	pF
C_{rss}	Reverse Transfer Capacitance		--	10	13	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 5.0\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	6.8	24	ns
t_r	Turn-On Rise Time		--	45	100	ns
$t_{d(off)}$	Turn-Off Delay Time		--	30	70	ns
t_f	Turn-Off Fall Time		--	40	90	ns
Q_g	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 5.0\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	12	16	nC
Q_{gs}	Gate-Source Charge		--	2.0	--	nC
Q_{gd}	Gate-Drain Charge		--	5.5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	4.6	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	18	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 4.6 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 5.0 A,	--	130	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs (Note 4)	--	0.58	--	μC

Notes:

1. Repetitive Rating ; Pulse width limited by maximum junction temperature
2. $L = 4.6\text{ mH}$, $I_{AS} = 4.6\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 5.0\text{ A}$, $dI/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

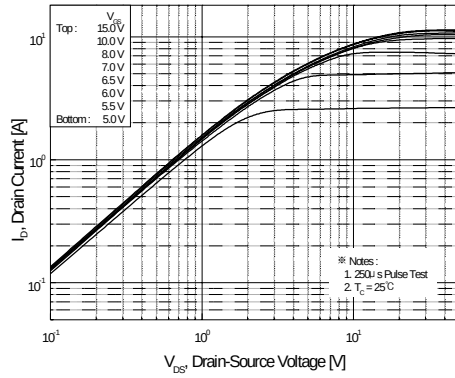


Figure 1. On-Region Characteristics

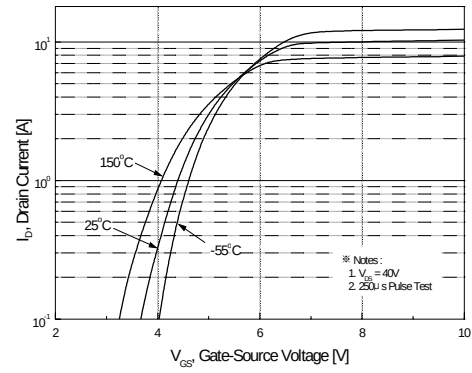


Figure 2. Transfer Characteristics

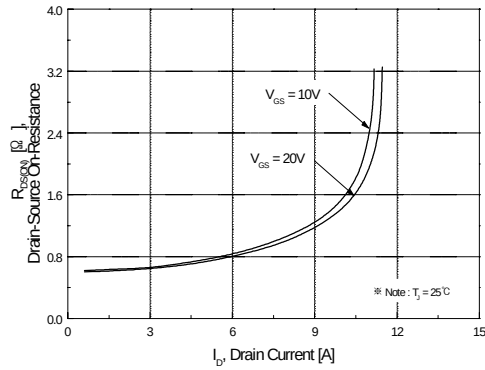


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

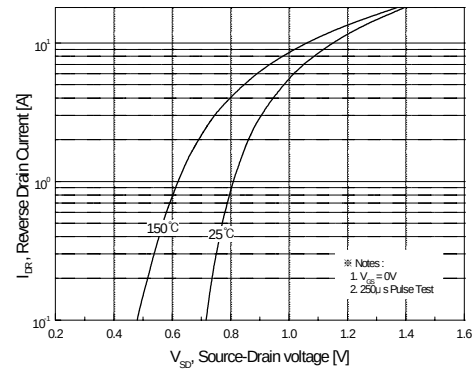


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

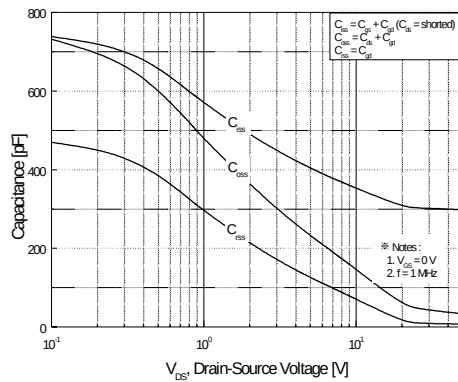


Figure 5. Capacitance Characteristics

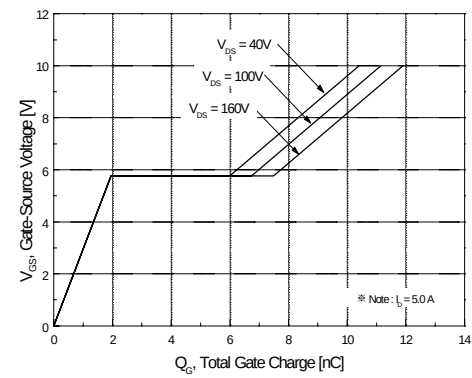


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

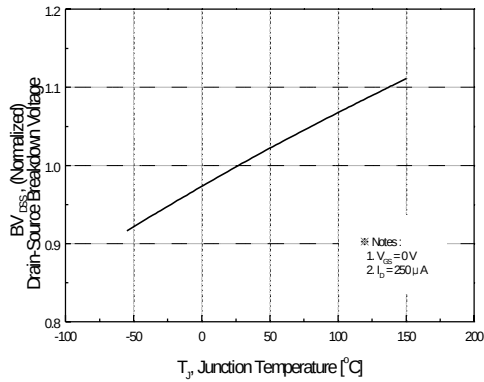


Figure 7. Breakdown Voltage Variation vs Temperature

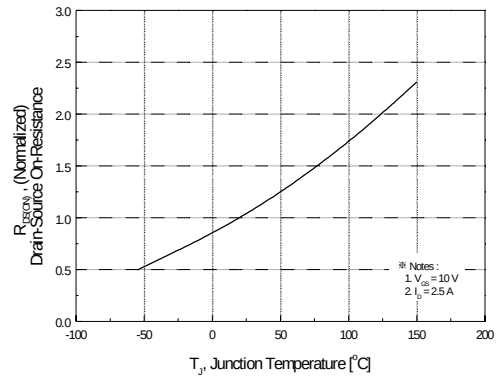


Figure 8. On-Resistance Variation vs Temperature

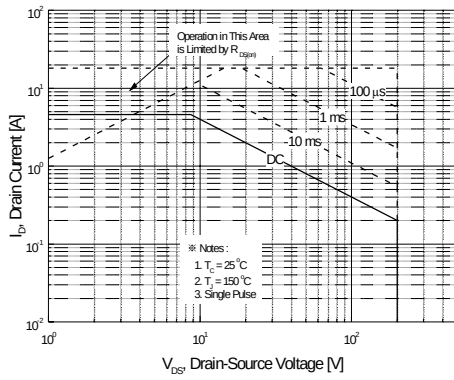


Figure 9. Maximum Safe Operating Area

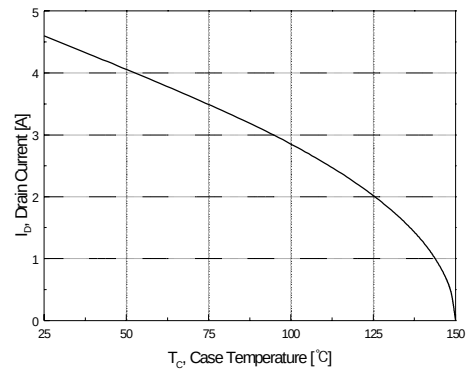


Figure 10. Maximum Drain Current vs Case Temperature

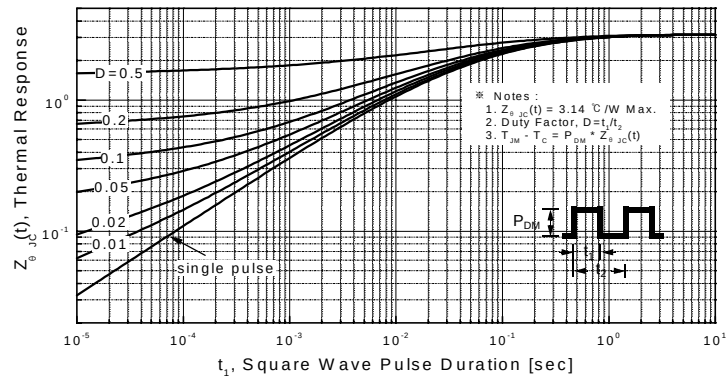
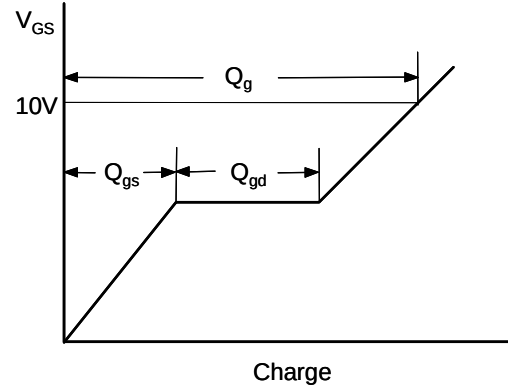
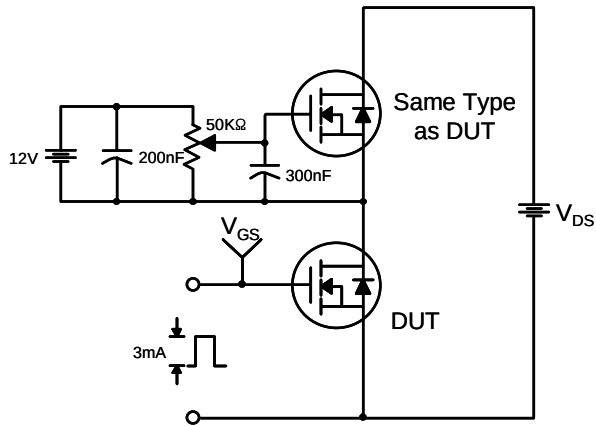
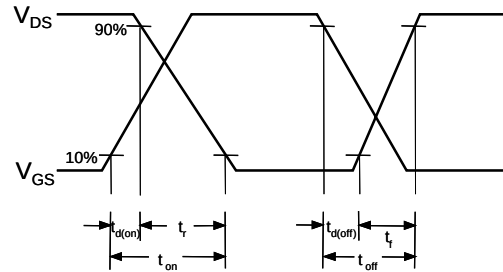
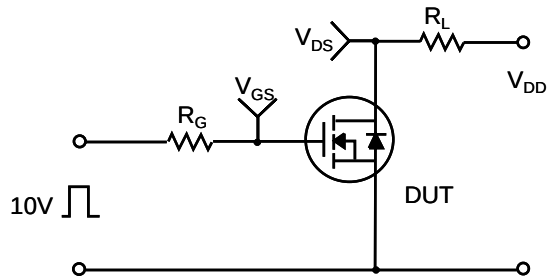


Figure 11. Transient Thermal Response Curve

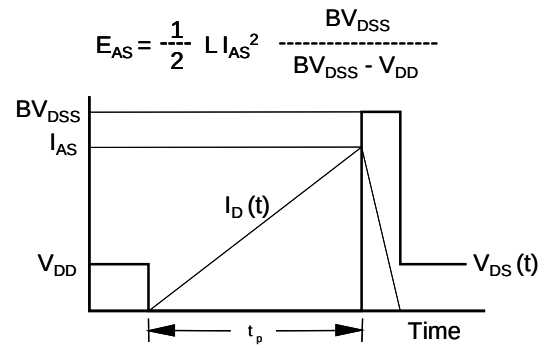
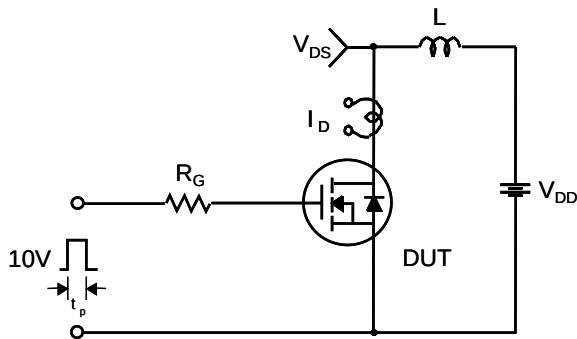
Gate Charge Test Circuit & Waveform



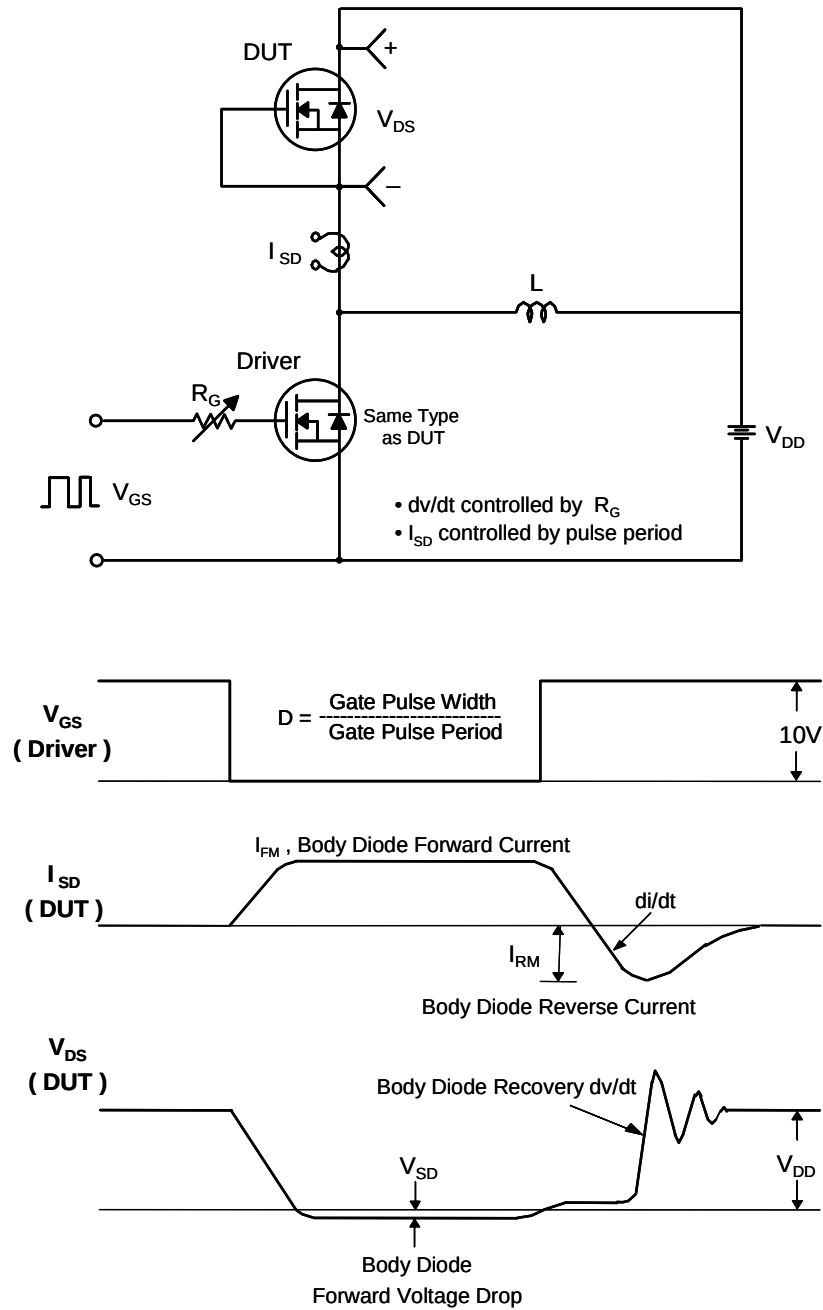
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

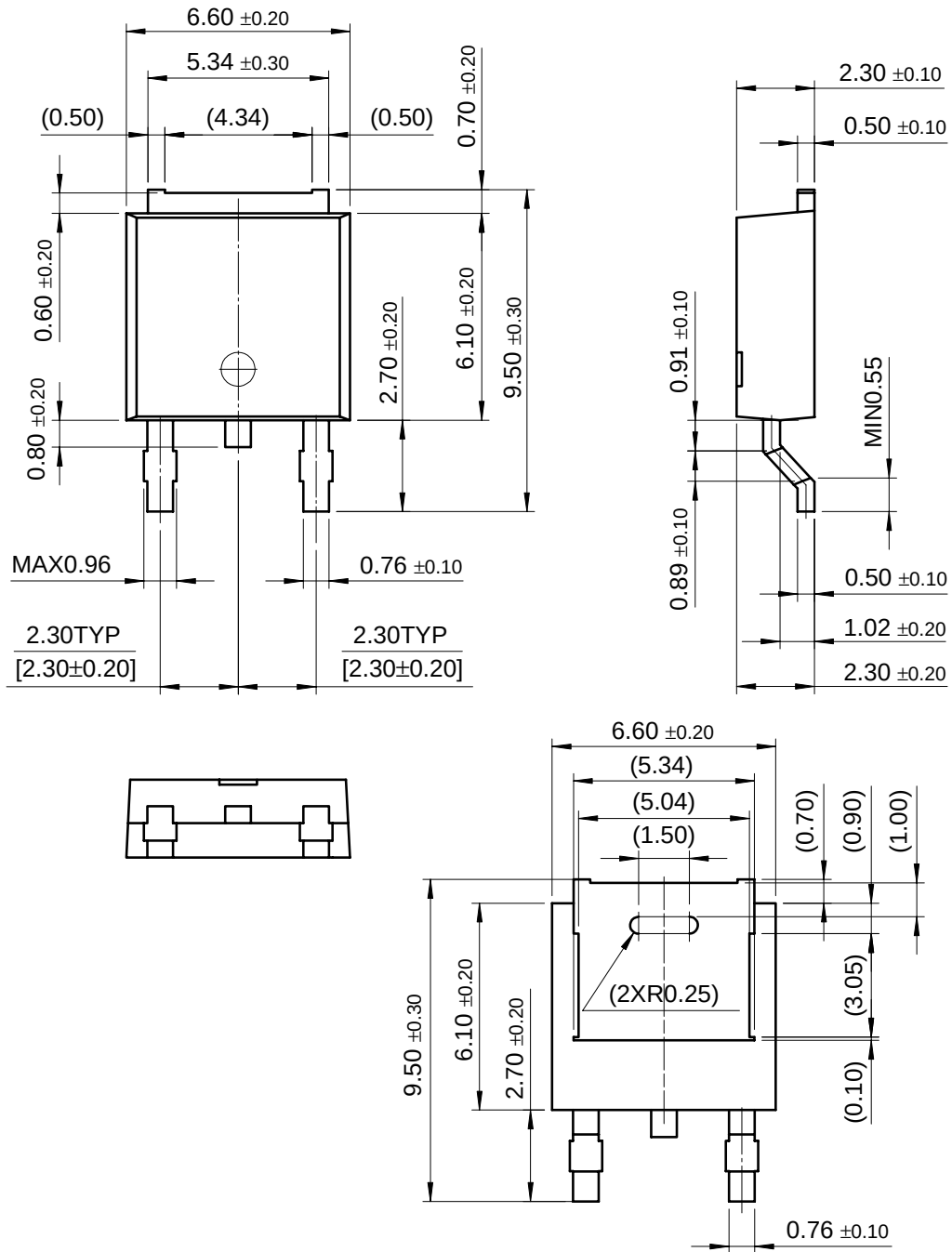


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

D-PAK



Dimensions in Millimeters

Technical drawing of a connector showing dimensions in millimeters. The drawing includes a top view, a side view, and a cross-sectional view.

Top View Dimensions:

- Overall width: 6.60 ± 0.20
- Inner width: 5.34 ± 0.20
- Side flange width (each side): (0.50)
- Central hole diameter: $\varnothing 0.60 \pm 0.20$
- Pin width (each pin): 0.80 ± 0.10
- Pin pitch (center-to-center): 1.80 ± 0.20
- Pin length: 9.30 ± 0.30
- Pin tip width: 0.76 ± 0.10
- Pin tip length: 0.76 ± 0.10
- Pin tip angle: $\text{MAX} 0.96^\circ$
- Pin tip radius: 2.30 TYP
- Pin tip width (each pin): $[2.30 \pm 0.20]$

Side View Dimensions:

- Overall height: 16.10 ± 0.30
- Top flange width: 2.30 ± 0.20
- Top flange thickness: 0.50 ± 0.10
- Pin length: 16.10 ± 0.30

Cross-sectional View:

- Shows the internal structure of the connector, including the central hole and the pin arrangement.

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